

IGBT MODULE (L series)

■ Features

- High Speed Switching
- Low Saturation Voltage
- Voltage Drive

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	1200	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	Continuous	I_C	25
	1ms	I_C pulse	50
	Continuous	$-I_C$	25
	1ms	$-I_C$ pulse	50
Max. Power Dissipation	P_C	250	W
Operating Temperature	T_j	+150	°C
Storage Temperature	T_{stg}	-40 to +125	°C
Isolation Voltage	AC. 1min.	V_{is}	2500
Screw Torque	Mounting *1	3.5	N · m

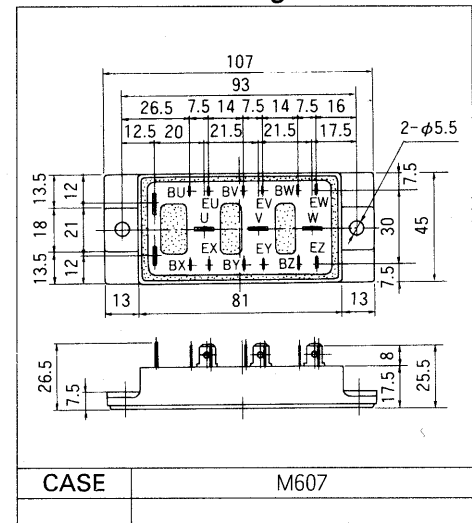
● Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0V$ $V_{CE}=1200V$ $T_j=25^\circ\text{C}$			1.0	mA
		$V_{GE}=0V$ $V_{CE}=1200V$ $T_j=125^\circ\text{C}$			—	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V$ $V_{GE}=\pm 20V$			100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=20V$ $I_C=25mA$	3.0		6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V$ $I_C=25A$		2.7	3.5	V
Input Capacitance	C_{ies}	$V_{GE}=0V$		4500		pF
Output Capacitance	C_{oes}	$V_{CE}=10V$		—		
Reverse Transfer Capacitance	C_{res}	$f=1MHz$		—		
Turn-on Time	t_{on}	$V_{CC}=600V$		0.5	0.8	μs
	t_r	$I_C=25A$		0.3	0.6	
Turn-off Time	t_{off}	$V_{GE}=\pm 15V$		0.8	1.5	
	t_f	$R_G=50\Omega$		0.3	0.5	
Diode Forward On-Voltage	V_F	$I_F=25A$ $V_{GE}=0V$			2.5	V
Reverse Recovery Time	t_{rr}	$I_F=25A$ $-di/dt=75A/\mu\text{s}$ $V_{GE}=-10V$		200	350	ns

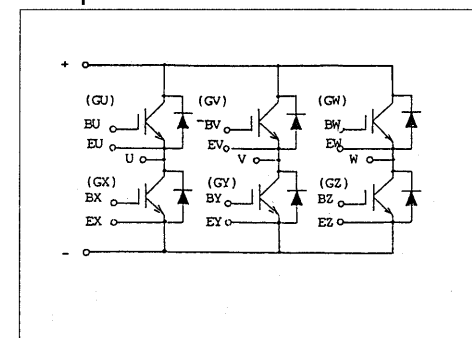
● Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.50	°C/W
	$R_{th(j-c)}$	Diode			1.00	
	$R_{th(c-f)}$	With Thermal compound		0.05		

■ Outline Drawings

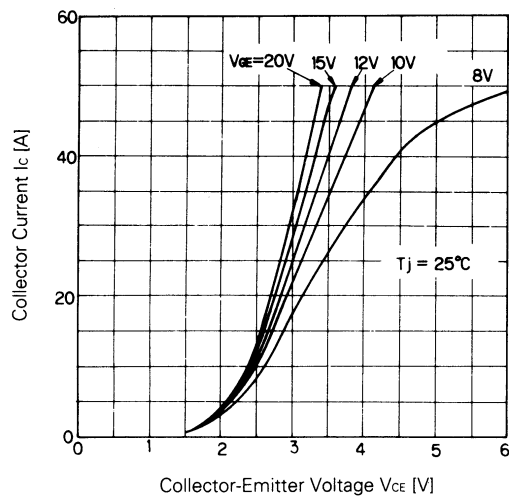


■ Equilavelent Circuit Schematic

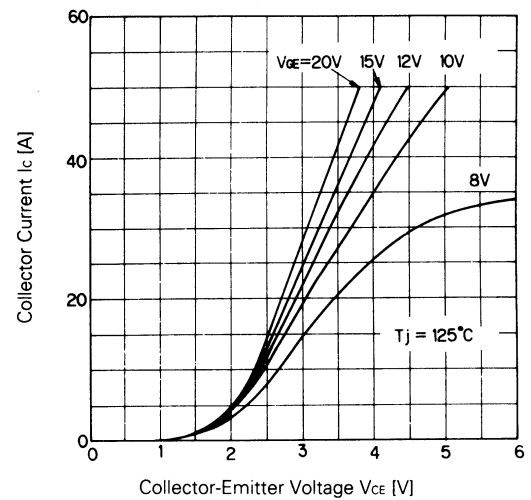


*1 Recommendable Value 2.5 ~ 3.5 N·m (M5)

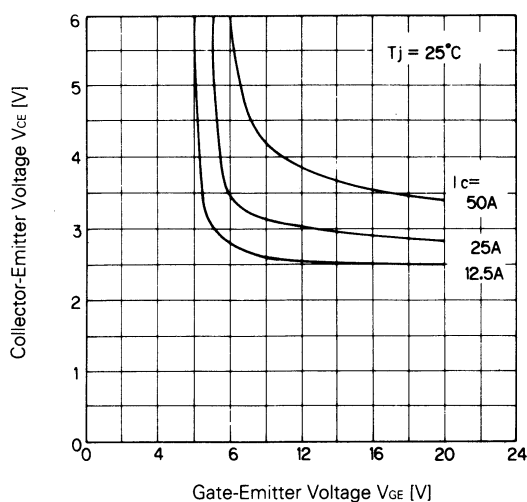
Characteristics



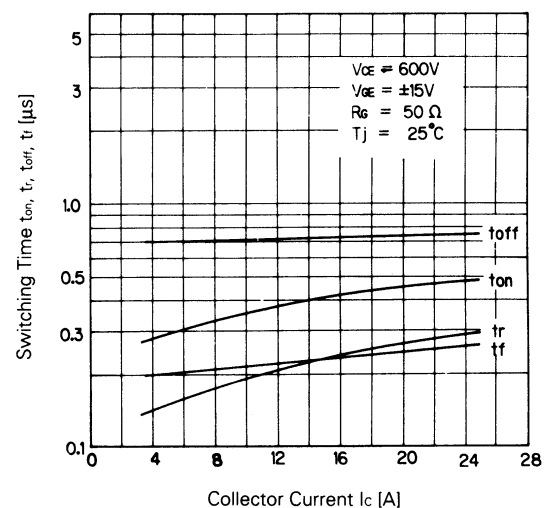
Collector Current vs. Collector-Emitter Voltage



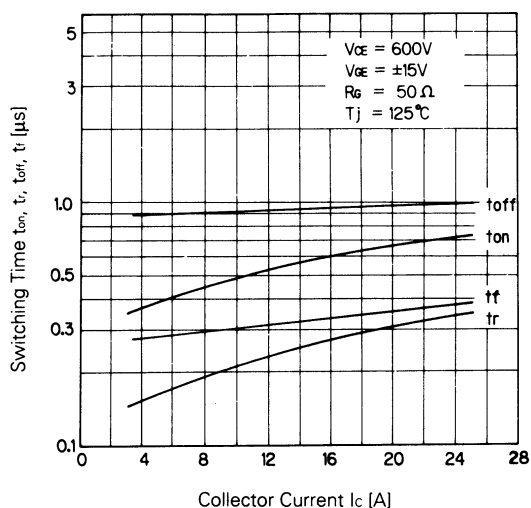
Collector Current vs. Collector-Emitter Voltage



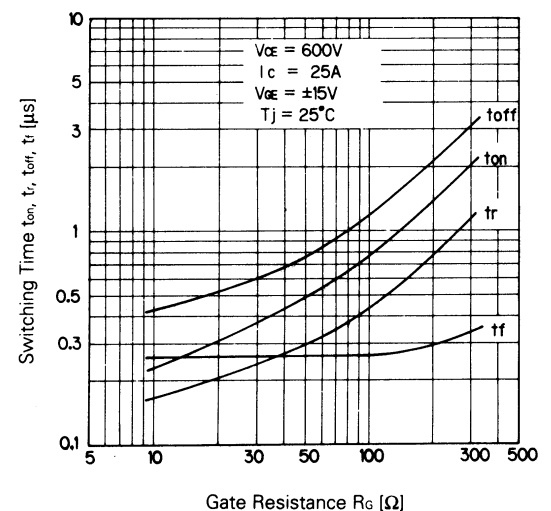
Collector-Emitter Voltage vs. Gate-Emitter Voltage



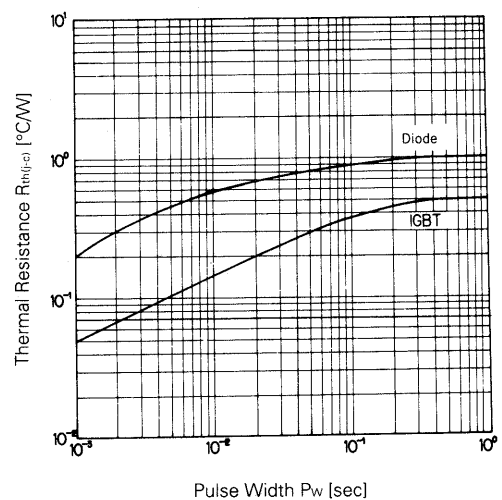
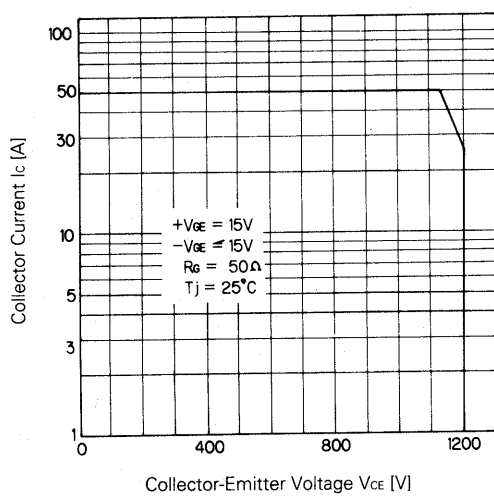
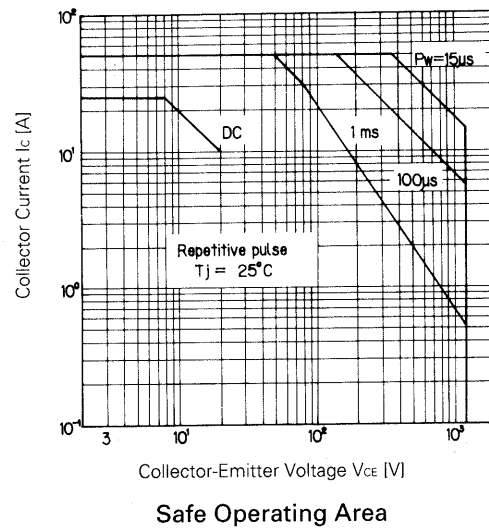
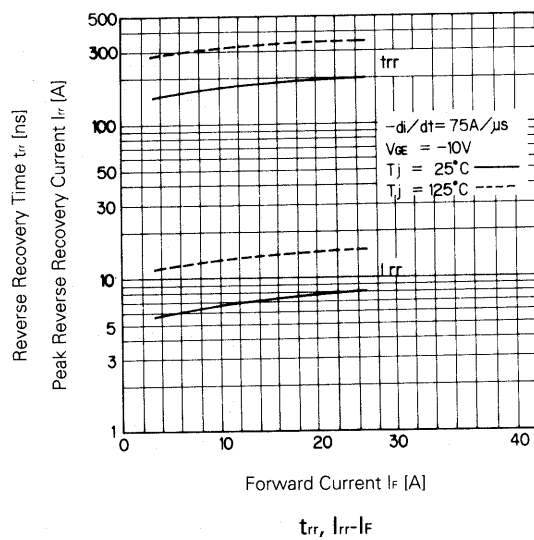
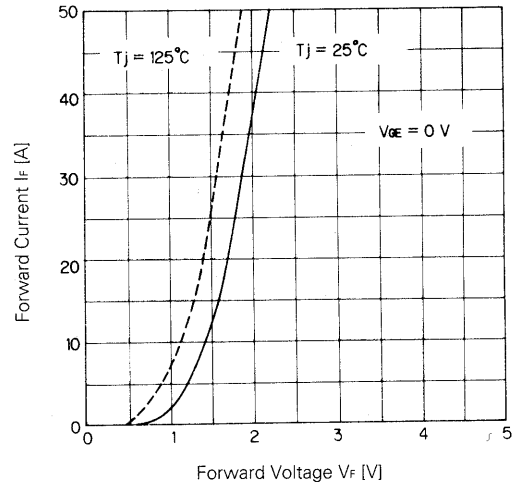
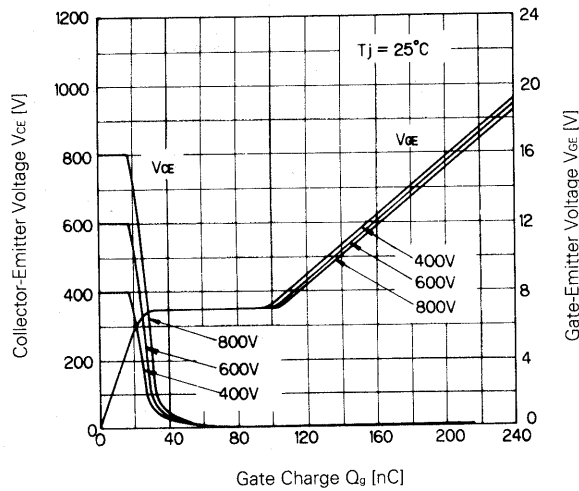
Switching Time



Switching Time



Switching Time-Gate Resistance



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